

II. Amendments to Claims:

1. (Original) A semiconductor comprising:
Subj
β1
a contact having a portion that extends on two opposing vertical sides of at least one vertical structure adjacent a gate electrode.

2. (Currently Amended) The semiconductor of claim 1, wherein the contact contacts a substrate adjacent the at least one spacer vertical structure.
α1

3. (Original) The semiconductor of claim 1, wherein the contact contacts the gate electrode.

4. (Original) The semiconductor of claim 1, wherein the contact includes an upper portion that is larger than a lower, contact portion.

Claims 5-20 (cancelled).

21. (New) The semiconductor of claim 1, wherein each vertical structure is a spacer.

22. (New) The semiconductor of claim 21, wherein the contact contacts a substrate adjacent one spacer.

23. (New) The semiconductor of claim 1, wherein the at least one vertical structure includes two vertical structures, one to each side of the gate electrode.

Sub 7
24. (New) The semiconductor of claim 23, wherein each vertical structure is a spacer.

At contact
25. (New) The semiconductor of claim 24, wherein the contact contacts a substrate adjacent one of the spacers.

26. (New) The semiconductor of claim 23, wherein the contact contacts the gate electrode.

27. (New) A semiconductor comprising:

a gate electrode;
a spacer to each side of the gate electrode; and
a contact having a portion that extends on two opposing vertical sides of at least one of the spacers.

28. (New) The semiconductor of claim 27, wherein the contact contacts a substrate adjacent one of the spacers.

29. (New) The semiconductor of claim 27, wherein the contact contacts the gate electrode.

30. (New) The semiconductor of claim 27, wherein the contact includes an upper portion that is larger than a lower, contact portion.

31. (New) A semiconductor comprising:

Sub B
B7

a gate electrode;

a spacer positioned on each side of the gate electrode; and

a contact having a portion that extends on two opposing vertical sides of each spacer.

A' Contact

32. (New) The semiconductor of claim 30, wherein the contact contacts the gate electrode.

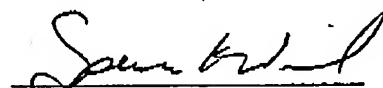
33. (New) The semiconductor of claim 30, wherein the contact includes an upper portion that is larger than a lower contact portion.

With regard to new claims 21-33, these claims are believed to be within the scope of Group I, claims 1-4.

Applicant has revised claim 2 to correct an informality and to place it in better form for examination. Since this revision was not made in response to a rejection, Applicants submit that the revision is not made to meet any requirements for patentability.

Should the Examiner require anything further from Applicants, the Examiner is invited to contact Applicants' undersigned representative at the number listed below.

Respectfully submitted,



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